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Kind regards,

Team Nexperia



# PMEG2010EPK

# 20 V, 1 A low VF MEGA Schottky barrier rectifier Rev. 2 — 14 March 2012

Product data sheet

## **Product profile**

## 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small SOD1608 (DFN1608D-2) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

#### 1.2 Features and benefits

- Average forward current: I<sub>F(AV)</sub> ≤ 1 A
- Reverse voltage: V<sub>R</sub> ≤ 20 V
- Low forward voltage V<sub>F</sub> ≤ 415 mV
- Low reverse current

- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package

## 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- LED backlight for mobile application
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

#### 1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions		Min	Тур	Max	Unit
average forward current	square wave; $\delta$ = 0.5; f = 20 kHz; T <sub>amb</sub> ≤ 110 °C	<u>[1]</u>	-	-	1	Α
	square wave; $\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 135 °C		-	-	1	Α
reverse voltage	T <sub>j</sub> = 25 °C		-	-	20	V
forward voltage	$I_F$ = 1 A; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C		-	370	415	mV
reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C		-	50	250	μA
reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$		-	4	-	ns
	average forward current  reverse voltage forward voltage reverse current	$\begin{array}{ll} \text{average forward} & \text{square wave; } \delta = 0.5;  f = 20   \text{kHz;} \\ T_{amb} \leq 110  ^{\circ}\text{C} \\ & \text{square wave; } \delta = 0.5;  f = 20   \text{kHz;} \\ T_{sp} \leq 135  ^{\circ}\text{C} \\ \\ \text{reverse voltage} & T_{j} = 25  ^{\circ}\text{C} \\ \\ \text{forward voltage} & I_{F} = 1  \text{A; pulsed; } t_{p} \leq 300   \mu\text{s; } \delta \leq 0.02; \\ T_{j} = 25  ^{\circ}\text{C} \\ \\ \text{reverse current} & V_{R} = 10   \text{V; } T_{j} = 25  ^{\circ}\text{C} \\ \\ \text{reverse recovery time} & I_{R} = 0.5   \text{A; } I_{R(meas)} = 0.1   \text{A;} \\ \end{array}$	$\begin{array}{ll} \text{average forward} & \text{square wave; } \delta = 0.5;  f = 20  \text{kHz;} \\ T_{amb} \leq 110  ^{\circ}\text{C} \\ \hline \text{square wave; } \delta = 0.5;  f = 20  \text{kHz;} \\ T_{sp} \leq 135  ^{\circ}\text{C} \\ \hline \text{reverse voltage} & T_{j} = 25  ^{\circ}\text{C} \\ \hline \text{forward voltage} & I_{F} = 1  \text{A; pulsed; } t_{p} \leq 300  \mu\text{s; } \delta \leq 0.02; \\ T_{j} = 25  ^{\circ}\text{C} \\ \hline \text{reverse current} & V_{R} = 10  \text{V; } T_{j} = 25  ^{\circ}\text{C} \\ \hline \text{reverse recovery time} & I_{R} = 0.5  \text{A; } I_{R(meas)} = 0.1  \text{A;} \\ \hline \end{array}$	$\begin{array}{lll} \text{average forward} & \text{square wave; } \delta = 0.5;  f = 20  \text{kHz;} & \\ \hline T_{amb} \leq 110  ^{\circ}\text{C} & \\ \hline \text{square wave; } \delta = 0.5;  f = 20  \text{kHz;} & \\ \hline T_{sp} \leq 135  ^{\circ}\text{C} & \\ \hline \text{reverse voltage} & T_{j} = 25  ^{\circ}\text{C} & \\ \hline \text{forward voltage} & I_{F} = 1  \text{A; pulsed; } t_{p} \leq 300  \text{\mus; } \delta \leq 0.02; \\ \hline T_{j} = 25  ^{\circ}\text{C} & \\ \hline \text{reverse current} & V_{R} = 10  \text{V; } T_{j} = 25  ^{\circ}\text{C} & \\ \hline \text{reverse recovery time} & I_{R} = 0.5  \text{A; } I_{R(meas)} = 0.1  \text{A;} & \\ \hline \end{array}$	$\begin{array}{c} \text{average forward} \\ \text{current} \\ \end{array} \begin{array}{c} \text{square wave; } \delta = 0.5;  f = 20 \text{ kHz;} \\ T_{amb} \leq 110  ^{\circ}\text{C} \\ \end{array} \\ \text{square wave; } \delta = 0.5;  f = 20 \text{ kHz;} \\ T_{sp} \leq 135  ^{\circ}\text{C} \\ \end{array} \\ \text{reverse voltage} \\ T_{j} = 25  ^{\circ}\text{C} \\ \text{forward voltage} \\ T_{j} = 1  \text{A; pulsed; } t_{p} \leq 300  \text{\mus; } \delta \leq 0.02; \\ T_{j} = 25  ^{\circ}\text{C} \\ \end{array} \\ \text{reverse current} \\ V_{R} = 10  \text{V; } T_{j} = 25  ^{\circ}\text{C} \\ \text{reverse recovery time} \\ I_{R} = 0.5  \text{A; } I_{R(meas)} = 0.1  \text{A;} \\ \end{array} \\ \begin{array}{c} 11 \\ - \\ - \\ 50 \\ \end{array} \\ \end{array}$	$\begin{array}{llllllllllllllllllllllllllllllllllll$

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		. 84 .
2	Α	anode	1 2	1 <del>    </del> 2 sym001
			Transparent top view	
			SOD1608 (DFN1608D-2)	)

<sup>[1]</sup> The marking bar indicates the cathode.

## 3. Ordering information

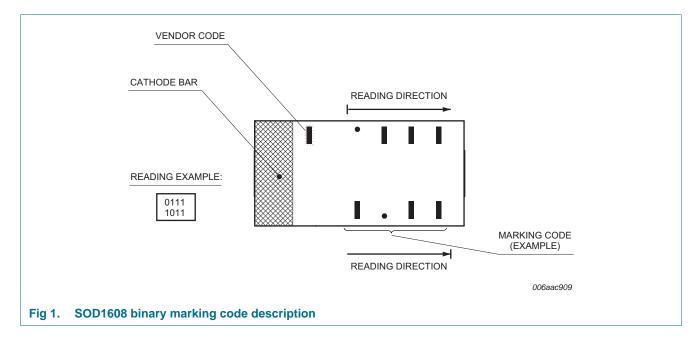
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG2010EPK	DFN1608D-2	Leadless ultra small plastic package; 2 terminals	SOD1608

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG2010EPK	0100 0000



## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_R$	reverse voltage	$T_j = 25  ^{\circ}C$		-	20	V
I <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 130 °C		-	1.4	Α
I <sub>F(AV)</sub>	average forward current	square wave; $\delta$ = 0.5; f = 20 kHz; T <sub>amb</sub> ≤ 110 °C	<u>[1]</u>	-	1	Α
		square wave; $\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 135 °C		-	1	Α
$I_{FRM}$	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.25$		-	3	Α
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; $t_p = 8 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$		-	5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	410	mW
			[3]	-	860	mW
			[1]	-	1565	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fr	thermal resistance	in free air	[1][2]	-	-	305	K/W
	from junction to ambient		[1][3]	-	-	145	K/W
	ambient		[1][4]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		<u>[5]</u>	-	-	20	K/W

<sup>[1]</sup> For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

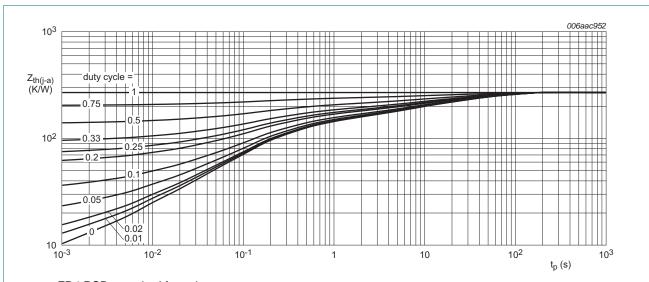
<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

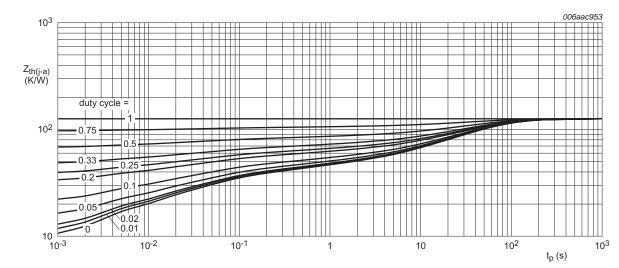
<sup>[4]</sup> Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

<sup>[5]</sup> Soldering point of cathode tab.



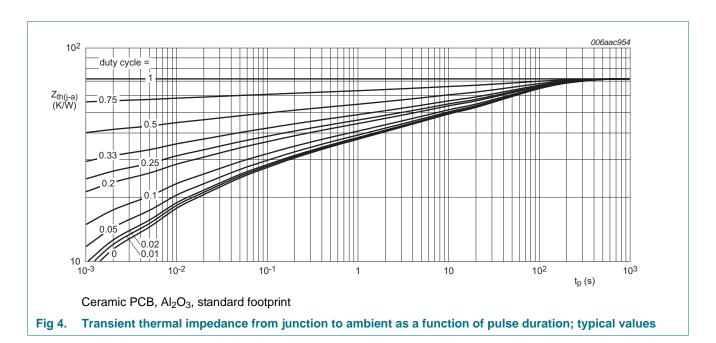
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

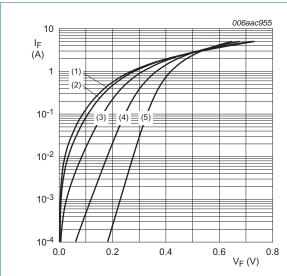
Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



## 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage	$I_F$ = 100 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C	-	240	280	mV
		$I_F$ = 500 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_j$ = 25 °C	-	310	350	mV
		$I_F$ = 700 mA; pulsed; $t_p \le 300 \mu s$ ; $δ \le 0.02$ ; $T_j$ = 25 °C	-	330	390	mV
		$I_F$ = 1 A; pulsed; $t_p \le 300 \text{ μs}$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C	-	370	415	mV
I <sub>R</sub> reverse current	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C	-	50	250	μA
		V <sub>R</sub> = 20 V; T <sub>j</sub> = 25 °C	-	150	600	μΑ
C <sub>d</sub>	diode capacitance	$V_R = 1 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$	-	65	-	pF
		$V_R = 10 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ °C}$	-	25	-	pF
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	4	-	ns
$V_{FRM}$	peak forward recovery voltage	$I_F = 0.5 \text{ A}; dI_F/dt = 20 \text{ A/}\mu\text{s}; T_j = 25 \text{ °C}$	-	335	-	mV



- (1)  $T_i = 150 \, ^{\circ}C$
- (2)  $T_i = 125 \, ^{\circ}C$
- (3)  $T_i = 85 \, ^{\circ}C$
- (4)  $T_j = 25 \, ^{\circ}C$
- (5)  $T_j = -40 \, ^{\circ}\text{C}$

Fig 5. Forward current as a function of forward voltage; typical values

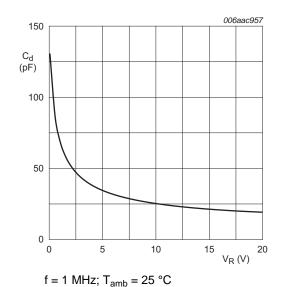
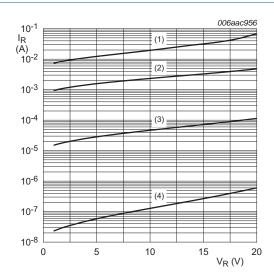
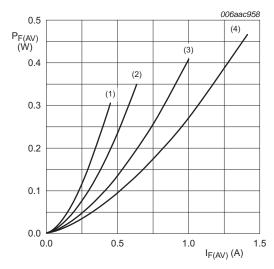


Fig 7. Diode capacitance as a function of reverse voltage; typical values



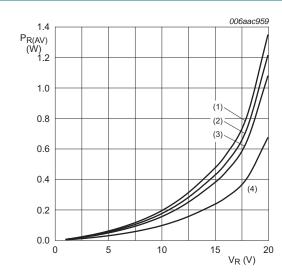
- (1)  $T_i = 125 \, ^{\circ}C$
- (2)  $T_i = 85 \, ^{\circ}C$
- (3)  $T_j = 25 \, {}^{\circ}\text{C}$
- (4)  $T_i = -40 \, ^{\circ}C$

Fig 6. Reverse current as a function of reverse voltage; typical values



- T<sub>i</sub> = 150 °C
- (1)  $\delta = 0.1$
- (2)  $\delta = 0.2$
- (3)  $\delta = 0.5$
- (4)  $\delta = 1$

Fig 8. Average forward power dissipation as a function of average forward current; typical values



T<sub>i</sub> = 125 °C

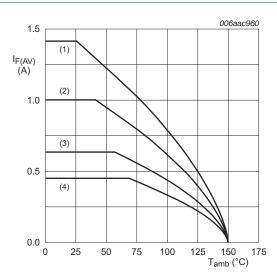
(1)  $\delta = 1$ 

(2)  $\delta = 0.9$ 

(3)  $\delta = 0.8$ 

(4)  $\delta = 0.5$ 

Fig 9. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

 $T_i = 150 \, ^{\circ}C$ 

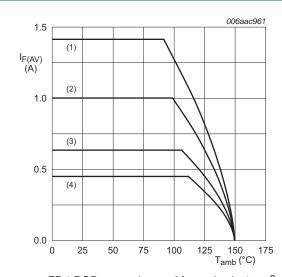
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 10. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

T<sub>i</sub> = 150 °C

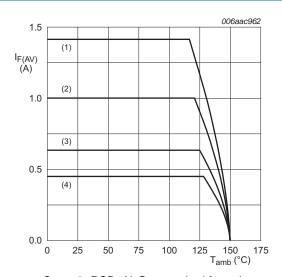
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

 $T_i = 150 \, ^{\circ}C$ 

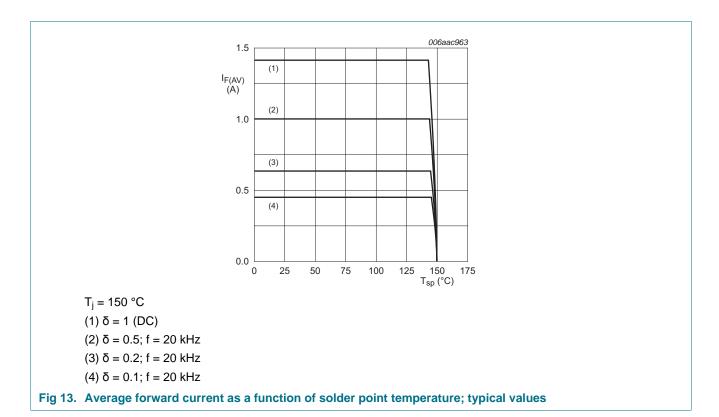
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

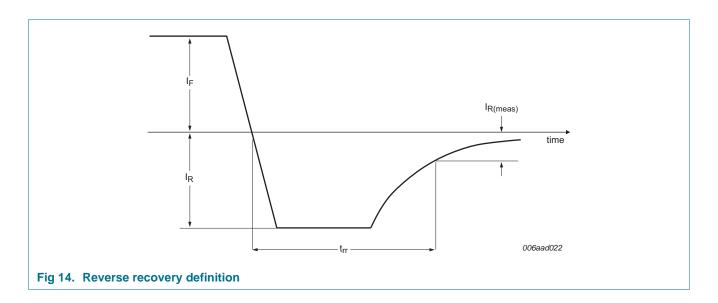
(3)  $\delta = 0.2$ ; f = 20 kHz

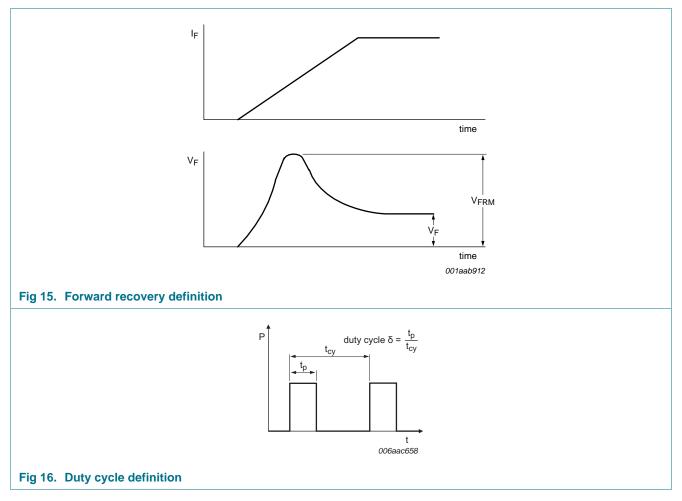
(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 12. Average forward current as a function of ambient temperature; typical values



## 8. Test information



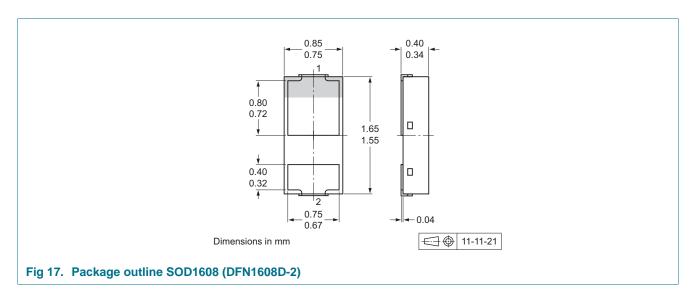


The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

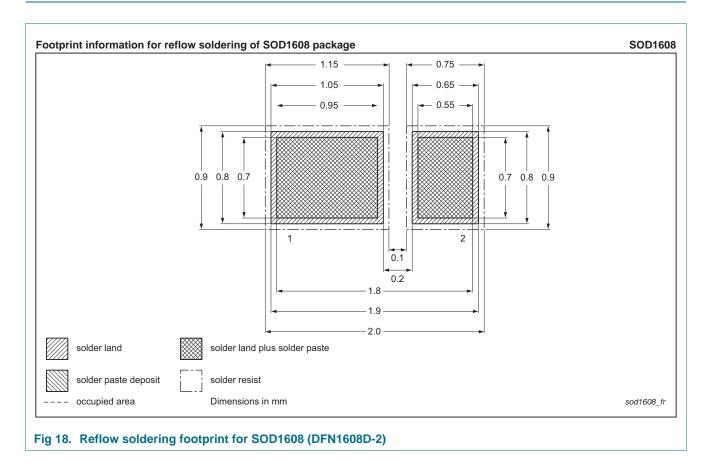
## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Soldering





## 11. Revision history

## Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Document 15	residude date	Data officer otatao	Change notice	ouperocues -
PMEG2010EPK v.2	20120314	Product data sheet	-	PMEG2010EPK v.1
Modifications:	• 5 "Limiting va	lues": I <sub>F</sub> corrected		
	• 7 "Characteris	stics": t <sub>rr</sub> and V <sub>FRM</sub> added		
	• <u>Fig 14.</u> and <u>1</u>	<u>5</u> : added		
PMEG2010EPK v.1	20120120	Product data sheet	-	-

## 12. Legal information

#### 12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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PMEG2010EPK

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#### 20 V, 1 A low VF MEGA Schottky barrier rectifier

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## 13. Contact information

For more information, please visit:http://www.nxp.com

For sales office addresses, please send an email to:salesaddresses@nxp.com

## PMEG2010EPK

## 20 V, 1 A low VF MEGA Schottky barrier rectifier

## 14. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking2
5	Limiting values3
6	Thermal characteristics3
7	Characteristics5
8	Test information8
8.1	Quality information
9	Package outline
10	Soldering10
11	Revision history11
12	Legal information12
12.1	Data sheet status
12.2	Definitions12
12.3	Disclaimers
12.4	Trademarks13
13	Contact information13

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